

L Number	Hits	Search Text	DB	Time stamp
-	3	HSG and hemispherical and electrode and (monolayer or monoatomiclayer or "mono-atomic layer" or "atomic layer") and semiconductor	USPAT; EPO; JPO; DERWENT	2004/03/10 12:59
-	0	HSG and hemispherical and electrode and ALCVD	USPAT; EPO; JPO; DERWENT	2001/03/21 14:58
-	0	HSG and hemispherical and ALCVD	USPAT; EPO; JPO; DERWENT	2001/03/21 14:58
-	0	HSG and hemispherical and ALCVD	USPAT; EPO; JPO; DERWENT	2001/03/21 14:58
-	0	HSG and ALCVD	USPAT; EPO; JPO; DERWENT	2001/03/21 14:58
-	4	ALCVD	USPAT; EPO; JPO; DERWENT	2001/03/21 14:59
-	0	HSG and grain\$1 and (dielectric adj1 layer) and monolayer\$1	USPAT; EPO; JPO; DERWENT	2001/03/21 15:01
-	0	HSG and grain\$1 and (dielectric adj1 layer) and (atomic adj1 layer)	USPAT; EPO; JPO; DERWENT	2001/03/21 15:17
-	691	HSG and hemispherical	USPAT; EPO; JPO; DERWENT	2001/03/21 15:17
-	224	(HSG and hemispherical) and nitride and oxide and metal	USPAT; EPO; JPO; DERWENT	2001/03/21 15:18
-	34	((HSG and hemispherical) and nitride and oxide and metal) and (multilayer or "multy-layer")	USPAT; EPO; JPO; DERWENT	2001/03/21 15:18
-	48	((HSG and hemispherical) and nitride and oxide and metal) and (multilayer or "multi-layer")	USPAT; EPO; JPO; DERWENT	2001/03/21 15:37
-	0	HSG and ALD	USPAT; EPO; JPO; DERWENT	2001/03/21 15:38
-	758	ALD	USPAT; EPO; JPO; DERWENT	2001/03/21 15:38
-	77	ALD and electrode\$1	USPAT; EPO; JPO; DERWENT	2001/03/22 08:59
-	3	((("5626906") or ("6124158") or ("6090659")).PN.	USPAT	2001/03/21 15:44
-	77	ALD and electrode\$1	USPAT; EPO; JPO; DERWENT	2001/03/22 09:11
-	1	("6090659").PN.	USPAT	2001/03/22 09:40
-	0	HSG and grain\$1 and hemisperical and (high adj1 dielectric adj1 constant)	USPAT; EPO; JPO; DERWENT	2001/03/22 09:41
-	0	HSG and hemisperical and (high adj1 dielectric adj1 constant)	USPAT; EPO; JPO; DERWENT	2001/03/22 09:42
-	1	HSG and hemisperical and (dielectric adj1 constant)	USPAT; EPO; JPO; DERWENT	2001/03/22 09:43
-	194	HSG and (dielectric adj1 constant)	USPAT; EPO; JPO; DERWENT	2001/03/22 09:43
-	126	HSG and (high adj1 dielectric adj1 constant)	USPAT; EPO; JPO; DERWENT	2001/03/22 09:43
-	110	(HSG and (high adj1 dielectric adj1 constant)) and electrode\$1	USPAT; EPO; JPO; DERWENT	2001/03/22 09:43

-	307036	((HSG and (high adj1 dielectric adj1 constant)) and electrode\$1) ang grain\$1	USPAT; EPO; JPO; DERWENT	2001/03/22 09:44
-	86	((HSG and (high adj1 dielectric adj1 constant)) and electrode\$1) and grain\$1	USPAT; EPO; JPO; DERWENT	2001/03/22 09:44
-	79	((HSG and (high adj1 dielectric adj1 constant)) and electrode\$1) and grain\$1) and hemispherical	USPAT; EPO; JPO; DERWENT	2001/03/22 14:49
-	15	WO93/12542	USPAT; EPO; JPO; DERWENT	2001/03/22 14:49
-	0	WO9312542	USPAT; EPO; JPO; DERWENT	2001/03/22 14:50
-	0	WO9312542.did.	USPAT; EPO; JPO; DERWENT	2001/03/22 14:50
-	0	W9312542.did.	USPAT; EPO; JPO; DERWENT	2001/03/22 14:50
-	0	WO9312542.did.	USPAT; EPO; JPO; DERWENT	2001/03/22 14:51
-	0	WO-9312542	USPAT; EPO; JPO; DERWENT	2001/03/22 14:51
-	1	9312542.did.	DERWENT	2001/03/22 14:51
-	411	(dielectric adj1 layer) with (Si or silicon) with (oxygen or oxide) with metal	USPAT; EPO; JPO; DERWENT	2003/10/17 16:06
-	19	(dielectric adj1 layer) with (Si or silicon) with (oxygen or oxide) with metal with CVD	USPAT; EPO; JPO; DERWENT	2001/03/23 10:24
-	14	semiconductor and (monolayers same (high with k with dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/10 15:27
-	187	capacitor and ALD	USPAT; EPO; JPO; DERWENT	2003/10/17 16:06
-	15	(capacitor and ALD) and HSG	USPAT; EPO; JPO; DERWENT	2003/10/17 16:37
-	13	semiconductor and ALD.ti.	USPAT; EPO; JPO; DERWENT	2003/10/17 16:38
-	5	(semiconductor and ALD.ti.) and purge	USPAT; EPO; JPO; DERWENT	2003/10/17 16:37
-	5	((semiconductor and ALD.ti.) and purge) and aluminum	USPAT; EPO; JPO; DERWENT	2003/10/17 16:37
-	33	ALD.ti.	USPAT; EPO; JPO; DERWENT	2003/10/17 16:38
-	28	ALD.ti. not (((semiconductor and ALD.ti.) and purge) and aluminum)	USPAT; EPO; JPO; DERWENT	2003/10/17 16:39
-	48	ALD and (PZT or BST)	USPAT; EPO; JPO; DERWENT	2003/10/20 14:03
-	28	(ALD and (PZT or BST)) and capacitor	USPAT; EPO; JPO; DERWENT	2003/10/20 14:04
-	5	(TaO or (tantalum adj pentoxide) or (tantalum adj oxide) or "TaO.sub.5") and ALD and HSG	USPAT; EPO; JPO; DERWENT	2004/03/09 19:49
-	4	(high with k with dielectric) and ALD and HSG	USPAT; EPO; JPO; DERWENT	2004/03/09 19:50

-	70	(high with k with dielectric) and ALD	USPAT; EPO; JPO; DERWENT	2004/03/09 19:51
-	30	((high with k with dielectric) and ALD) and monolayer\$1	USPAT; EPO; JPO; DERWENT	2004/03/09 19:56
-	1	HSG and (high with k) same (silicon same oxygen same metal)	USPAT; EPO; JPO; DERWENT	2004/03/09 19:58
-	1	HSG and (high with k) same (si same oxygen same metal)	USPAT; EPO; JPO; DERWENT	2004/03/09 19:58
-	1	HSG and (high with k) same (si same metal same oxide)	USPAT; EPO; JPO; DERWENT	2004/03/09 20:06
-	3	HSG and (high with k) same (MIS)	USPAT; EPO; JPO; DERWENT	2004/03/09 20:07
-	6	HSG and (high with k) same (MIM\$1)	USPAT; EPO; JPO; DERWENT	2004/03/09 20:07
-	57	HSG and (MIM\$1 or MIS)	USPAT; EPO; JPO; DERWENT	2004/03/09 20:16
-	19	(US-5463235-\$ or US-5444653-\$ or US-6521943-\$ or US-6489214-\$ or US-6387761-\$ or US-6372598-\$ or US-6335240-\$ or US-6281142-\$ or US-6204203-\$ or US-6159793-\$ or US-6144062-\$ or US-6074913-\$ or US-6057205-\$ or US-6037235-\$ or US-5998264-\$ or US-5994197-\$ or US-5726085-\$ or US-5723373-\$ or US-6589839-\$).did.	USPAT	2004/03/09 20:15
-	0	((US-5463235-\$ or US-5444653-\$ or US-6521943-\$ or US-6489214-\$ or US-6387761-\$ or US-6372598-\$ or US-6335240-\$ or US-6281142-\$ or US-6204203-\$ or US-6159793-\$ or US-6144062-\$ or US-6074913-\$ or US-6057205-\$ or US-6037235-\$ or US-5998264-\$ or US-5994197-\$ or US-5726085-\$ or US-5723373-\$ or US-6589839-\$).did.) and monolayer\$1	USPAT; EPO; JPO; DERWENT	2004/03/09 20:16
-	2	((US-5463235-\$ or US-5444653-\$ or US-6521943-\$ or US-6489214-\$ or US-6387761-\$ or US-6372598-\$ or US-6335240-\$ or US-6281142-\$ or US-6204203-\$ or US-6159793-\$ or US-6144062-\$ or US-6074913-\$ or US-6057205-\$ or US-6037235-\$ or US-5998264-\$ or US-5994197-\$ or US-5726085-\$ or US-5723373-\$ or US-6589839-\$).did.) and ALD	USPAT; EPO; JPO; DERWENT	2004/03/09 20:16
-	2	((US-5463235-\$ or US-5444653-\$ or US-6521943-\$ or US-6489214-\$ or US-6387761-\$ or US-6372598-\$ or US-6335240-\$ or US-6281142-\$ or US-6204203-\$ or US-6159793-\$ or US-6144062-\$ or US-6074913-\$ or US-6057205-\$ or US-6037235-\$ or US-5998264-\$ or US-5994197-\$ or US-5726085-\$ or US-5723373-\$ or US-6589839-\$).did.) and (ALD or (atomic adj layer))	USPAT; EPO; JPO; DERWENT	2004/03/09 20:16
-	0	ALD and (metal adj ethoxide)	USPAT; EPO; JPO; DERWENT	2004/03/10 12:59
-	32	ALD and (ethoxide)	USPAT; EPO; JPO; DERWENT	2004/03/10 13:02
-	296	monolayer\$1 and (ethoxide)	USPAT; EPO; JPO; DERWENT	2004/03/10 13:04
-	1	(monolayer\$1 and (ethoxide)) and HSG	USPAT; EPO; JPO; DERWENT	2004/03/10 13:03

-	0	(HSG or (hemispherical adj grain)) and (metal adj siloxane)	USPAT; EPO; JPO; DERWENT	2004/03/10 13:05
-	0	(HSG or (hemispherical adj grain)) and (silicon adj metiloxide)	USPAT; EPO; JPO; DERWENT	2004/03/10 13:05
-	0	(HSG or (hemispherical adj grain)) and (silicon adj metaloxide)	USPAT; EPO; JPO; DERWENT	2004/03/10 13:05
-	0	(HSG or (hemispherical adj grain)) and (silicon adj metal adj oxide)	USPAT; EPO; JPO; DERWENT	2004/03/10 16:03